

MEMORY

Un-buffered

4 M × 64 BIT SYNCHRONOUS DYNAMIC RAM DIMM

MB8504S064AC-100/-84/-67

168-pin, 2-clock, 2-bank, based on 2 M × 8 BIT SDRAMs with SPD

DESCRIPTION

The Fujitsu MB8504S064AC is a fully decoded, CMOS Synchronous Dynamic Random Access Memory (SDRAM) Module consisting of sixteen MB81117822A devices which organized as two banks of 2 M × 8 bits and a 2K-bit serial EEPROM on a 168-pin glass-epoxy substrate.

The MB8504S064AC features a fully synchronous operation referenced to a positive edge clock whereby all operations are synchronized at a clock input which enables high performance and simple user interface coexistence.

The MB8504S064AC is optimized for those applications requiring high speed, high performance and large memory storage, and high density memory organizations.

This module is ideally suited for workstations, PCs, laser printers, and other applications where a simple interface is needed.

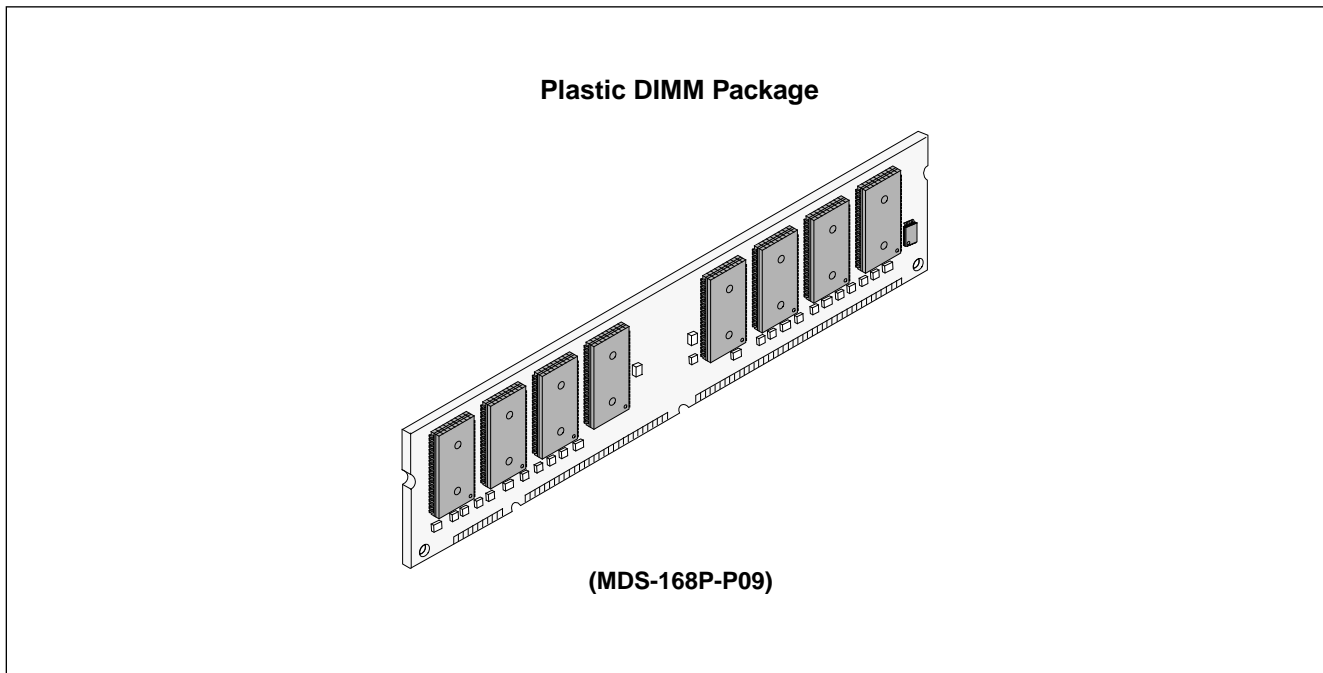
PRODUCT LINE & FEATURES

Parameter		MB8504S064AC-100	MB8504S064AC-84	MB8504S064AC-67
Clock Frequency		100 MHz max.	84 MHz max.	67 MHz max.
Burst Mode Cycle Time		10 ns max. (CL = 3) 15 ns max. (CL = 2)	12 ns max. (CL = 3) 17 ns max. (CL = 2)	15 ns max. (CL = 3) 20 ns max. (CL = 2)
RAS Access Time		54 ns max.	56 ns max.	60 ns max.
CAS Access Time		24 ns max.	26 ns max.	30 ns max.
Output Valid from Clock		8.5 ns max. (CL = 3) 9 ns max. (CL = 2)	8.5 ns max. (CL = 3) 9 ns max. (CL = 2)	9 ns max. (CL = 3) 10 ns max. (CL = 2)
Power Dissipation	Burst Mode	4752 mW max.	4464 mW max.	4176 mW max.
	Power Down Mode	115.2 mW max.		

- Un-buffered 168-pin DIMM Socket Type (Lead pitch : 1.27 mm)
- Conformed to JEDEC Standard (2 CLK)
- Organization : 4,194,304 words × 64 bits
- Memory : MB81117822A (2 M × 8, 2-bank) × 16 pcs.
- 3.3 V ± 0.3 V Supply Voltage
- All input/output LVTTTL compatible
- 2048 Refresh Cycle every 32.8 ms
- Auto and Self Refresh
- CKE Power Down Mode
- DQM Byte Masking (Read/Write)
- Serial Presence Detect (SPD) with Serial EEPROM
- Module size : 1.0" (height) × 5.25" (length) × 0.157" (thick)

MB8504S064AC-100/-84/-67

■ PACKAGE



Package and Ordering Information

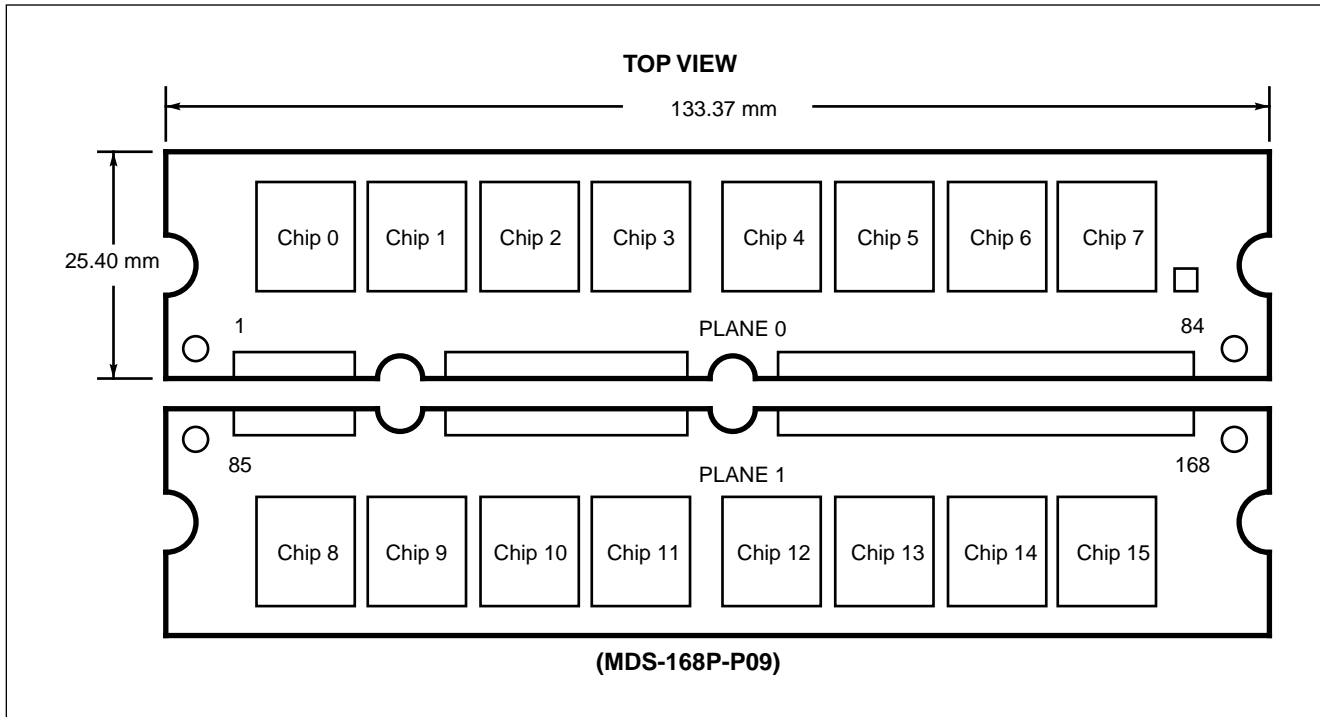
– 168-pad DIMM, order as MB8504S064AC-xxDG (DG = Gold Pad)

MB8504S064AC-100/-84/-67

■ PIN ASSIGNMENTS

Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name	Pin No.	Signal Name
1	V _{SS}	29	DQMB ₁	57	DQ ₁₈	85	V _{SS}	113	DQMB ₅	141	DQ ₅₀
2	DQ ₀	30	\overline{CS}_0	58	DQ ₁₉	86	DQ ₃₂	114	\overline{CS}_1	142	DQ ₅₁
3	DQ ₁	31	N.C.	59	V _{CC}	87	DQ ₃₃	115	\overline{RAS}	143	V _{CC}
4	DQ ₂	32	V _{SS}	60	DQ ₂₀	88	DQ ₃₄	116	V _{SS}	144	DQ ₅₂
5	DQ ₃	33	A ₀	61	N.C.	89	DQ ₃₅	117	A ₁	145	N.C.
6	V _{CC}	34	A ₂	62	N.C.	90	V _{CC}	118	A ₃	146	N.C.
7	DQ ₄	35	A ₄	63	N.C.	91	DQ ₃₆	119	A ₅	147	N.C.
8	DQ ₅	36	A ₆	64	V _{SS}	92	DQ ₃₇	120	A ₇	148	V _{SS}
9	DQ ₆	37	A ₈	65	DQ ₂₁	93	DQ ₃₈	121	A ₉	149	DQ ₅₃
10	DQ ₇	38	A ₁₀	66	DQ ₂₂	94	DQ ₃₉	122	A ₁₁	150	DQ ₅₄
11	DQ ₈	39	N.C.	67	DQ ₂₃	95	DQ ₄₀	123	N.C.	151	DQ ₅₅
12	V _{SS}	40	V _{CC}	68	V _{SS}	96	V _{SS}	124	V _{CC}	152	V _{SS}
13	DQ ₉	41	V _{CC}	69	DQ ₂₄	97	DQ ₄₁	125	CLK ₁	153	DQ ₅₆
14	DQ ₁₀	42	CLK ₀	70	DQ ₂₅	98	DQ ₄₂	126	N.C.	154	DQ ₅₇
15	DQ ₁₁	43	V _{SS}	71	DQ ₂₆	99	DQ ₄₃	127	V _{SS}	155	DQ ₅₈
16	DQ ₁₂	44	N.C.	72	DQ ₂₇	100	DQ ₄₄	128	CKE	156	DQ ₅₉
17	DQ ₁₃	45	\overline{CS}_2	73	V _{CC}	101	DQ ₄₅	129	\overline{CS}_3	157	V _{CC}
18	V _{CC}	46	DQMB ₂	74	DQ ₂₈	102	V _{CC}	130	DQMB ₆	158	DQ ₆₀
19	DQ ₁₄	47	DQMB ₃	75	DQ ₂₉	103	DQ ₄₆	131	DQMB ₇	159	DQ ₆₁
20	DQ ₁₅	48	N.C.	76	DQ ₃₀	104	DQ ₄₇	132	N.C.	160	DQ ₆₂
21	N.C.	49	V _{CC}	77	DQ ₃₁	105	N.C.	133	V _{CC}	161	DQ ₆₃
22	N.C.	50	N.C.	78	V _{SS}	106	N.C.	134	N.C.	162	V _{SS}
23	V _{SS}	51	N.C.	79	N.C.	107	V _{SS}	135	N.C.	163	N.C.
24	N.C.	52	N.C.	80	N.C.	108	N.C.	136	N.C.	164	N.C.
25	N.C.	53	N.C.	81	N.C.	109	N.C.	137	N.C.	165	SA ₀
26	V _{CC}	54	V _{SS}	82	SDA	110	V _{CC}	138	V _{SS}	166	SA ₁
27	\overline{WE}	55	DQ ₁₆	83	SCL	111	\overline{CAS}	139	DQ ₄₈	167	SA ₂
28	DQMB ₀	56	DQ ₁₇	84	V _{CC}	112	DQMB ₄	140	DQ ₄₉	168	V _{CC}

MB8504S064AC-100/-84/-67



■ PIN DESCRIPTIONS

Symbol	I/O	Function	Symbol	I/O	Function
A ₀ to A ₁₁	I	Address Input	DQ ₀ to DQ ₆₃	I/O	Data Input/Data Output
$\overline{\text{RAS}}$	I	Row Address Strobe	V _{CC}	—	Power Supply (+3.3 V)
$\overline{\text{CAS}}$	I	Column Address Strobe	V _{SS}	—	Ground (0 V)
$\overline{\text{WE}}$	I	Write Enable	N.C.	—	No Connection
DQMB ₀ to DQMB ₇	I	Data (DQ) Mask	SA ₀ to SA ₂	I	Serial PD Address Input
CLK ₀ , CLK ₁	I	Clock Input	SCL	I	Serial PD Clock
CKE	I	Clock Enable	SDA	I/O	Serial PD Address/Data Input/Output
$\overline{\text{CS}}_0$ to $\overline{\text{CS}}_3$	I	Chip Select			

■ SERIAL-PD INFORMATION

Byte	Function Described		Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
0	Defines Number of Bytes Written into Serial Memory at Module Manufacture	128 Byte	1	0	0	0	0	0	0	0
1	Total Number of Bytes of SPD Memory	256 Byte	0	0	0	0	1	0	0	0
2	Fundamental Memory Type	SDRAM	0	0	0	0	0	1	0	0
3	Number of Row Addresses	11	0	0	0	0	1	0	1	1
4	Number of Column Addresses	9	0	0	0	0	1	0	0	1
5	Number of Module Banks	2 bank	0	0	0	0	0	0	1	0
6	Data Width	64 bit	0	1	0	0	0	0	0	0
7	Data Width (Continuation)	+0	0	0	0	0	0	0	0	0
8	Interface Type	LVTTL	0	0	0	0	0	0	0	1
9	SDRAM Cycle Time	10 ns	1	0	1	0	0	0	0	0
		12 ns	1	1	0	0	0	0	0	0
		15 ns	1	1	1	1	0	0	0	0
10	SDRAM Access from Clock	8.5 ns	1	0	0	0	0	1	0	1
		9 ns	1	0	0	1	0	0	0	0
11	DIMM Configuration Type	Non-Parity	0	0	0	0	0	0	0	0
12	Refresh Rate/Type	Self, Norm	1	0	0	0	0	0	0	0
13	SDRAM Module Attributes	UN-Buffer	0	0	0	0	0	0	0	0
14	SDRAM Device Attributes	(*)	0	0	0	0	0	1	1	0
15	Minimum Clock Delay Back to Back Random Column Address	1 Cycle	0	0	0	0	0	0	0	1
16	Burst Lengths Supported	1, 2, 4, 8	0	0	0	0	1	1	1	1
17	Number of Banks on Each SDRAM Device	2 bank	0	0	0	0	0	0	1	0
18	CAS Latency	2, 3	0	0	0	0	0	1	1	0
19	CS Latency	0	0	0	0	0	0	0	0	1
20	Write Latency	0	0	0	0	0	0	0	0	1
21 to 31	Reserved for Future Offerings	–	0	0	0	0	0	0	0	0
32 to 63	Superset Information	–	0	0	0	0	0	0	0	0
64 to 125	Manufacturer's Information	–	0	0	0	0	0	0	0	0
126	Intel Specification Frequency	66 MHz	0	1	1	0	0	1	1	0
127	Intel Specification CAS Latency	2, 3	0	0	0	0	0	1	1	0
128+	Unused Storage Locations	–	–	–	–	–	–	–	–	–

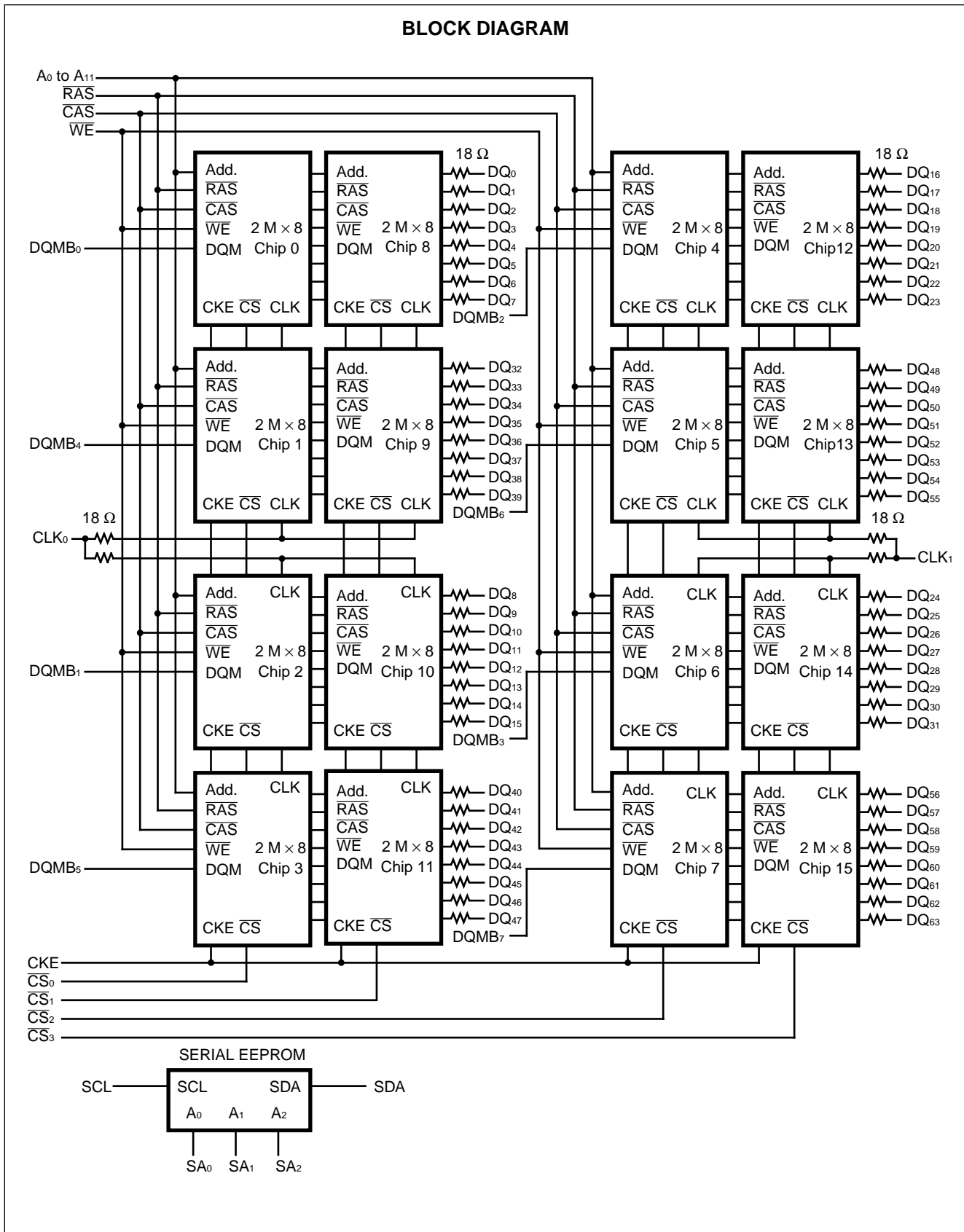
Note: Any write operation must NOT be executed into the addresses of Byte 0 to Byte 127. Some or all data stored into Byte 0 to Byte 127 may be broken.

(*) Byte 14 : SDRAM Device Attributes

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
TBD	TBD	TBD	TBD	Supported Single Write/ Burst Read	Supported Precharge All	Supported Auto- Precharge	Supported Early RAS Precharge
0	0	0	0	0	1	1	0

MB8504S064AC-100/-84/-67

BLOCK DIAGRAM



MB8504S064AC-100/-84/-67

■ ABSOLUTE MAXIMUM RATINGS (See WARNING)

Parameter	Symbol	Value		Unit
		Min.	Max.	
Supply Voltage*	V _{CC}	-0.5	+4.6	V
Input Voltage*	V _{IN}	-0.5	+4.6	V
Output Voltage*	V _{OUT}	-0.5	+4.6	V
Storage Temperature	T _{STG}	-55	+125	°C
Power Dissipation	P _D	—	10.2	W
Output Current (D.C.)	I _{OUT}	-50	+50	mA

* : Voltages referenced to V_{SS} (= 0 V)

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Notes	Symbol	Value			Unit
			Min.	Typ.	Max.	
Supply Voltage	*1	V _{CC}	3.0	3.3	3.6	V
		V _{SS}	0	0	0	V
Input High Voltage, all inputs	*1	V _{IH}	2.0	—	V _{CC} +0.5	V
Input Low Voltage, all inputs	*1, 2	V _{IL}	-0.5	—	0.8	V
Ambient Temperature		T _A	0	—	+70	°C

*1. Voltages referenced to V_{SS} (= 0 V)

*2. V_{IL} (min) = -1.5 V AC (Pulse Width ≤ 5 ns)

WARNING: Recommended operating conditions are normal operating ranges for the semiconductor device. All the device's electrical characteristics are warranted when operated within these ranges.

Always use semiconductor devices within the recommended operating conditions. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representative beforehand.

MB8504S064AC-100/-84/-67

■ CAPACITANCE

($V_{CC} = +3.3\text{ V}$, $f = 1\text{ MHz}$, $T_A = +25^\circ\text{C}$)

Parameter		Symbol	Value		Unit
			Min.	Max.	
Input Capacitance	A_0 to A_{11}	C_{IN1}	—	72	pF
	\overline{RAS} , \overline{CAS} , \overline{WE}	C_{IN2}	—	68	pF
	\overline{CS}_0 , \overline{CS}_3	C_{IN3}	—	24	pF
	CKE	C_{IN4}	—	73	pF
	CLK_0 , CLK_1	C_{IN5}	—	42	pF
	$DQMB_0$ to $DQMB_7$	C_{IN6}	—	17	pF
	SCL	C_{SCL}	—	6	pF
	SA_0 , SA_1 , SA_2	C_{SA}	—	6	pF
Input/Output Capacitance	SDA	C_{SDA}	—	7	pF
	DQ_0 to DQ_{63}	C_{DQ}	—	21	pF

MB8504S064AC-100/-84/-67

■ DC CHARACTERISTICS

(At recommended operating conditions unless otherwise noted.)

Parameter	Notes	Symbol	Condition	Value		Unit	
				Min.	Max.		
Operating Current (Average Power Supply Current)	*2	MB8504S064AC-100	No Burst; $t_{CK} = \min$ $t_{RC} = \min$ One Bank Active	—	920	mA	
		MB8504S064AC-84			880	mA	
		MB8504S064AC-67			840	mA	
		MB8504S064AC-100	No Burst; $t_{CK} = \min$ $t_{RC} = \min$ All Banks Active	—	1280	mA	
		MB8504S064AC-84			1200	mA	
		MB8504S064AC-67			1120	mA	
Precharge Standby Current (Power Supply Current)	*2	I_{CC2P}	CKE = V_{IL} , $t_{CK} = \min$ All Banks Idle	—	32	mA	
		I_{CC2N}	CKE = V_{IH} , $t_{CK} = \min$ All Banks Idle	—	480	mA	
Active Standby Current (Power Supply Current)	*2	I_{CC3P}	CKE = V_{IL} , $t_{CK} = \min$ Any Bank Active	—	480	mA	
		I_{CC3N}	CKE = V_{IH} , $t_{CK} = \min$ Any Bank Active	—	640	mA	
Burst Mode Current (Average Power Supply Current)	*2	MB8504S064AC-100	I_{CC4}	$t_{CK} = \min$	—	1320	mA
		MB8504S064AC-84			—	1240	mA
		MB8504S064AC-67			—	1160	mA
Auto-refresh Current (Average Power Supply Current)	*2	MB8504S064AC-100	I_{CC5}	Auto Refresh $t_{CK} = \min$ $t_{RC} = \min$ $t_{RRD} = \min$	—	1360	mA
		MB8504S064AC-84			—	1280	mA
		MB8504S064AC-67			—	1200	mA
Self-refresh Current (Average Power Supply Current)		I_{CC6}	$t_{CK} = V_{IL}$	—	32	mA	
Input Leakage Current (All Inputs)		$I_{I(L)}$	$0 V \leq V_{IN} \leq V_{CC}$ All other pins not under test = 0 V $3.0 V \leq V_{CC} \leq 3.6 V$	-80	80	μA	
Output Leakage Current		$I_{O(L)}$	Output is disabled (Hi-Z) $0 V \leq V_{OUT} \leq V_{CC}$ $3.0 V \leq V_{CC} \leq 3.6 V$	-20	20	μA	
LVTTL Output High Voltage	*1	V_{OH}	$I_{OH} = -2.0 \text{ mA}$	2.4	—	V	
LVTTL Output Low Voltage	*1	V_{OL}	$I_{OL} = +2.0 \text{ mA}$	—	0.4	V	

Notes: *1. Voltages referenced to V_{SS} (= 0 V)

*2. I_{CC} depends on the output termination, load conditions, clock cycle rate and signal clock rate.
The specified values are obtained with the output open and no termination register.

*3. An initial pause (DESL on NOP) of 200 μs is required after power-on followed by a minimum of eight Auto-refresh cycles.

*4. Values except I_{CC2P} are for when one side of the double-sided module is in standby mode and the other side has two banks active in burst mode.

*5. DC characteristics is the Serial PD standby state ($V_{IN} = GND$ or V_{CC}).

MB8504S064AC-100/-84/-67

■ AC CHARACTERISTICS

(1) BASE CHARACTERISTICS

(At recommended operating conditions unless otherwise noted.)

No.	Parameter	Notes	Symbol	MB8504S064AC -100		MB8504S064AC -84		MB8504S064AC -67		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	
1	Clock Period	CL = 3	t _{CK}	10	—	12	—	15	—	ns
		CL = 2		15	—	17	—	20	—	ns
2	Clock High Time		t _{CH}	4	—	4	—	4	—	ns
3	Clock Low Time		t _{CL}	4	—	4	—	4	—	ns
4	$\overline{\text{CS}}$ Set Up Time		t _{SC}	3	—	3	—	3	—	ns
5	$\overline{\text{CS}}$ Hold Time		t _{HC}	1	—	1	—	1	—	ns
6	Input Set Up Time		t _{SI}	3	—	3	—	3	—	ns
7	Input Hold Time		t _{HI}	1	—	1	—	1	—	ns
8	Data Input Set Up Time		t _{SID}	3	—	3	—	3	—	ns
9	Data Input Hold Time		t _{HID}	1	—	1	—	1	—	ns
10	Output Valid from Clock (t _{CLK} = min)	*1, *2 CL = 3	t _{AC}	—	8.5	—	8.5	—	9	ns
		CL = 2		—	9	—	9	—	10	
11	Output in Low-Z		t _{OLZ}	3	—	3	—	3	—	ns
12	Output in High-Z	*3	t _{OHZ}	3	—	3	—	3	—	ns
13	Output Hold Time		t _{OH}	3	—	3	—	3	—	ns
14	Time between Refresh		t _{REF}	—	32.8	—	32.8	—	32.8	ms
15	Transition Time		t _T	0.5	2	0.5	2	0.5	2	ns
16	Power Down Exit Time		t _{PDE}	3	—	4	—	5	—	ns

MB8504S064AC-100/-84/-67

(2) BASE VALUES FOR CLOCK COUNT/LATENCY

No.	Parameter	Notes	Symbol	MB8504S064AC -100		MB8504S064AC -84		MB8504S064AC -67		Unit
				Min.	Max.	Min.	Max.	Min..	Max.	
1	RAS Cycle Time	*4	t _{RC}	90	—	100	—	110	—	ns
2	RAS Access Time	*5	t _{RAC}	—	54	—	56	—	60	ns
3	CAS Access Time	*6, *9	t _{CAC}	—	24	—	26	—	30	ns
4	RAS Precharge Time		t _{RP}	30	—	35	—	40	—	ns
5	RAS Active Time		t _{RAS}	60	100000	65	100000	70	100000	ns
6	RAS to CAS Delay Time	*7	t _{RCD}	30	—	30	—	30	—	ns
7	Write Recovery Time		t _{WR}	10	—	12	—	15	—	ns
8	Write Precharge Time		t _{RWL}	10	—	12	—	15	—	ns
9	RAS to CAS Bank Active Delay Time		t _{RRD}	30	—	30	—	30	—	ns

(3) CLOCK COUNT FORMULA (*8)

$$\text{Clock} \geq \frac{\text{Base Value}}{\text{Clock Period}} \quad (\text{Round off a whole number})$$

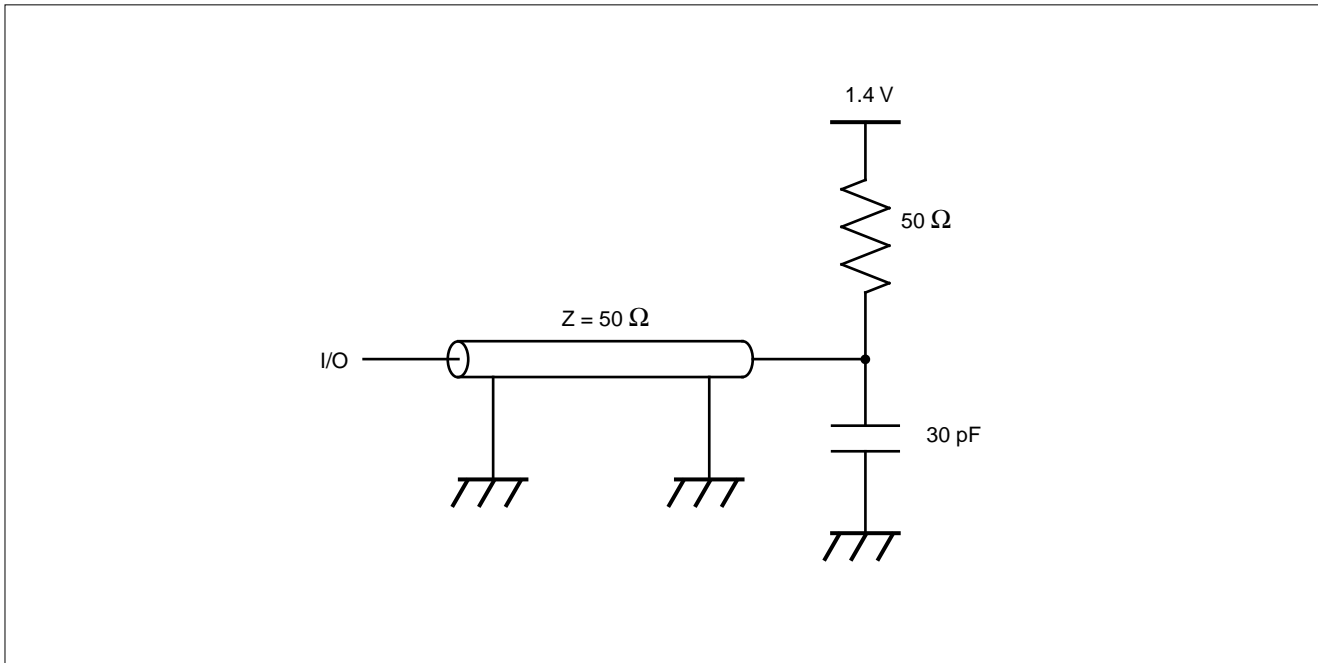
(4) LATENCY (The latency values on these parameters are fixed regardless of clock period.)

No.	Parameter	Symbol	MB8504S064AC -100	MB8504S064AC -84	MB8504S064AC -67	Unit
1	CKE to Clock Disable	t _{CKE}	1	1	1	Cycle
2	DQM to Output in High-Z	t _{DQZ}	2	2	2	Cycle
3	DQM to Input Data Delay	t _{DQD}	0	0	0	Cycle
4	Last Output to Write Command Delay	t _{LOWD}	2	2	2	Cycle
5	Write Command to Input Data Delay	t _{DWD}	0	0	0	Cycle
6	Precharge to Output in High-Z Delay	CL = 3	3	3	3	Cycle
		CL = 2	2	2	2	Cycle
7	Mode Register Access to Bank Active (min)	t _{MRD}	2	2	2	Cycle
8	CAS to CAS Delay (min)	t _{CCD}	1	1	1	Cycle
9	CAS Bank Delay (min)	t _{CBD}	1	1	1	Cycle

MB8504S064AC-100/-84/-67

- Notes:**
- *1. Assumes t_{RCD} and t_{CAC} are satisfied.
 - *2. t_{AC} also specifies the access time at burst mode except for first access.
 - *3. Specified where output buffer is no longer driven.
 - *4. Actual clock count of t_{RC} (I_{RC}) will be sum of clock count of t_{RAS} (I_{RAS}) and t_{RP} (I_{RP}).
 - *5. t_{RAC} is a reference value. Maximum value is obtained from the sum of t_{RCD} (min) and t_{CAC} (max).
 - *6. Assumes t_{RAC} and t_{AC} are satisfied.
 - *7. Operation within the t_{RCD} (min) ensures that t_{RAC} can be met; if t_{RCD} is greater than the specified t_{RCD} (min), access time is determined by t_{CAC} and t_{AC} .
 - *8. All base values are measured from the clock edge at the command input to the clock edge for the next command input.
All clock counts are calculated by a simple formula :
clock count equals base value divided by clock period (round off to a whole number).
 - *9. The t_{CAC} (CAS latency : CL) is programmed by the mode register.
 - *10. An initial pause (DESL on NOP) of 200 μ s is required after power-up followed by a minimum of eight Auto-refresh cycles.
 - *11. 1.4 V or V_{REF} is the reference level for measuring timing of signals.
Transition times are measured between V_{IH} (min) and V_{IL} (max).
 - *12. AC characteristics assume $t_r = 1$ ns and 30 pF of capacitive load.
- *Source : See MB811171822A Data Sheet for details on the electricals.

■ AC OPERATING TEST CONDITION (Example of AC Test Load Circuit)



ACKNOWLEDGE

Acknowledge is a software convention used to indicate successful data transfer. The transmitting device, either master or slave, will release the bus after transmitting eight bits. During the ninth clock cycle the receiver will put the SDA line to Low in order to acknowledge that it received the eight bits of data.

The SPD will respond with an acknowledge when it received the start condition followed by slave address issued by master.

In the read operation, the SPD will transmit eight bits of data, release the SDA line and monitor the line for an acknowledge. If an acknowledge is detected and no stop condition is issued by master, the SPD will continue to transmit data. If an acknowledge is not detected, the SPD will terminated further data transmissions. The master must then issue a stop condition to return the SPD to the standby power mode.

In the write operation, upon receipt of eight bits of data the SPD will respond with an acknowledge, and await the next eight bits of data, again responding with an acknowledge until the stop condition is issued by master.

SLAVE ADDRESS ADDRESSING

Following a start condition, the master must output the eight bits slave address. The most significant four bits of the slave address are device type identifier. For the SPD this is fixed as 1010[B]. Refer to the Fig.2 below.

The next three significant bits are used to select a particular device. A system could have up to eight SPD devices—namely up to eight modules—on the bus. The eight addresses for eight SPD devices are defined by the state of the SA0, SA1 and SA2 inputs.

The last bit of the slave address defines the operation to be performed. When R/\bar{W} bit is “1”, a read operation is selected, when R/\bar{W} bit is “0”, a write operation is selected.

Following the start condition, the SPD monitors the SDA line comparing the slave address being transmitted with its slave address (device type and state of SA0, SA1, and SA2 inputs). Upon a correct compare the SPD outputs an acknowledge on the SDA line. Depending on the state of the R/\bar{W} bit, the SPD will execute a read or write operation.

Fig.2 – SLAVE ADDRESS

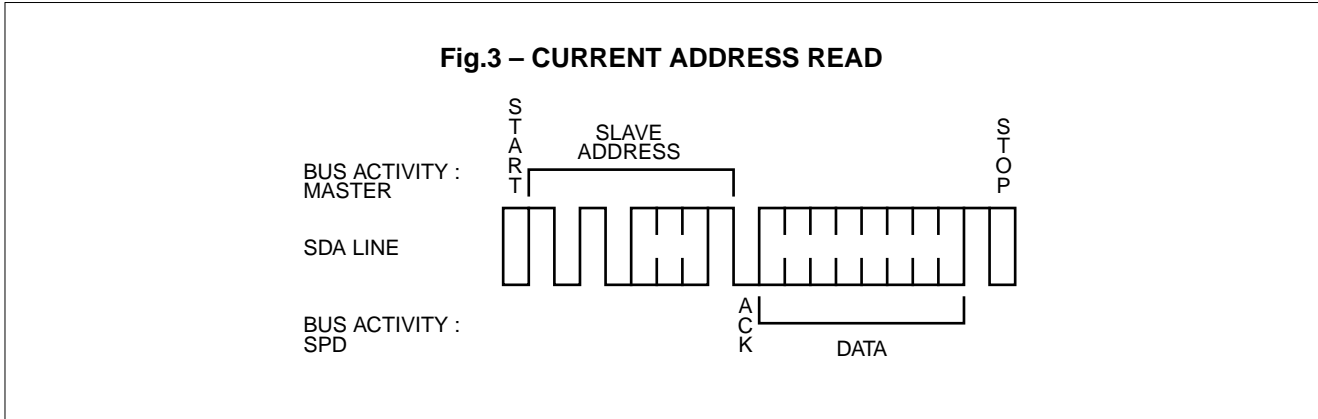
DEVICE TYPE IDENTIFIER				DEVICE ADDRESS			
1	0	1	0	SA ₂	SA ₁	SA ₀	R/ \bar{W}

MB8504S064AC-100/-84/-67

3. READ OPERATIONS

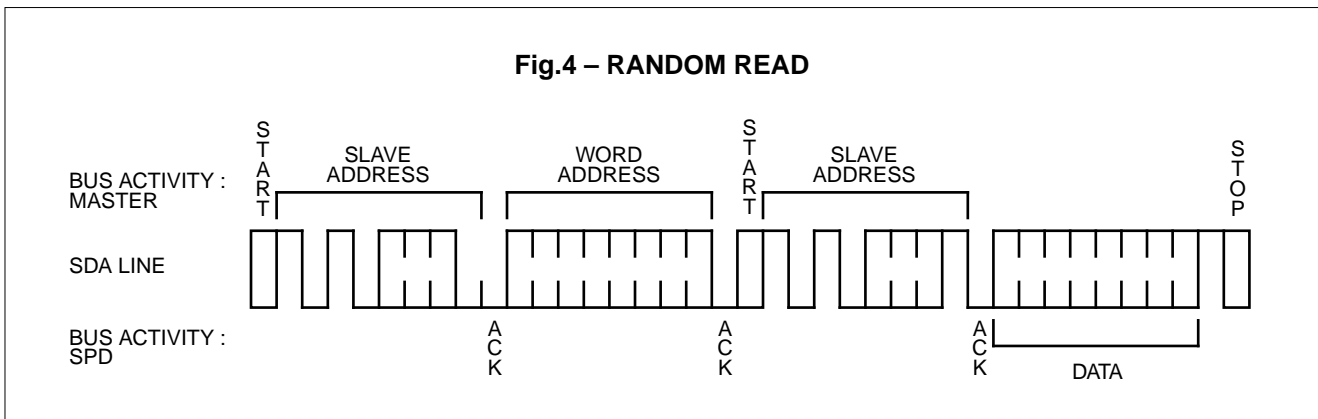
CURRENT ADDRESS READ

Internally the SPD contains an address counter that maintains the address of the last data accessed, incremented by one. Therefore, if the last access (either a read or write operation) was to address(n), the next read operation would access data from address(n+1). Upon receipt of the slave address with the R/\bar{W} bit = "1", the SPD issues an acknowledge and transmits the eight bits of data during the next eight clock cycles. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig.3 for the sequence of address, acknowledge and data transfer.



RANDOM READ

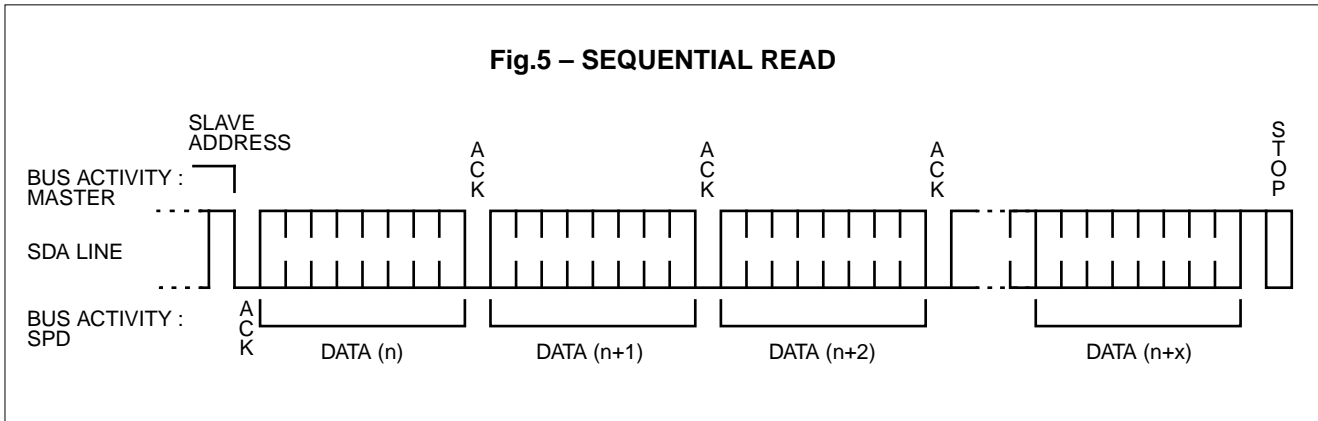
Random Read operations allow the master to access any memory location in a random manner. Prior to issuing the slave address with the R/\bar{W} bit = "1", the master must first perform a "dummy" write operation on the SPD. The master issues the start condition, and the slave address followed by the word address. After the word address acknowledge, the master immediately reissues the start condition and the slave address with the R/\bar{W} bit = "1". This will be followed by an acknowledge from the SPD and then by the eight bits of data. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig.4 for the sequence of address, acknowledge and data transfer.



SEQUENTIAL READ

Sequential Read can be initiated as either a current address read or random read. The first data are transmitted as with the other read mode, however, the master now responds with an acknowledge, indicating it requires additional data. The SPD continues to output data for each acknowledge received. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig.5 for the sequence of address, acknowledge and data transfer.

The data output is sequential, with the data from address(n) followed by the data from address(n+1). The address counter for read operations increments all address bits, allowing the entire memory contents to be serially read during one operation. At the end of the address space (address 255), the counter “rolls over” to address 0 and the SPD continues to output data for each acknowledge received.



4. DC CHARACTERISTICS

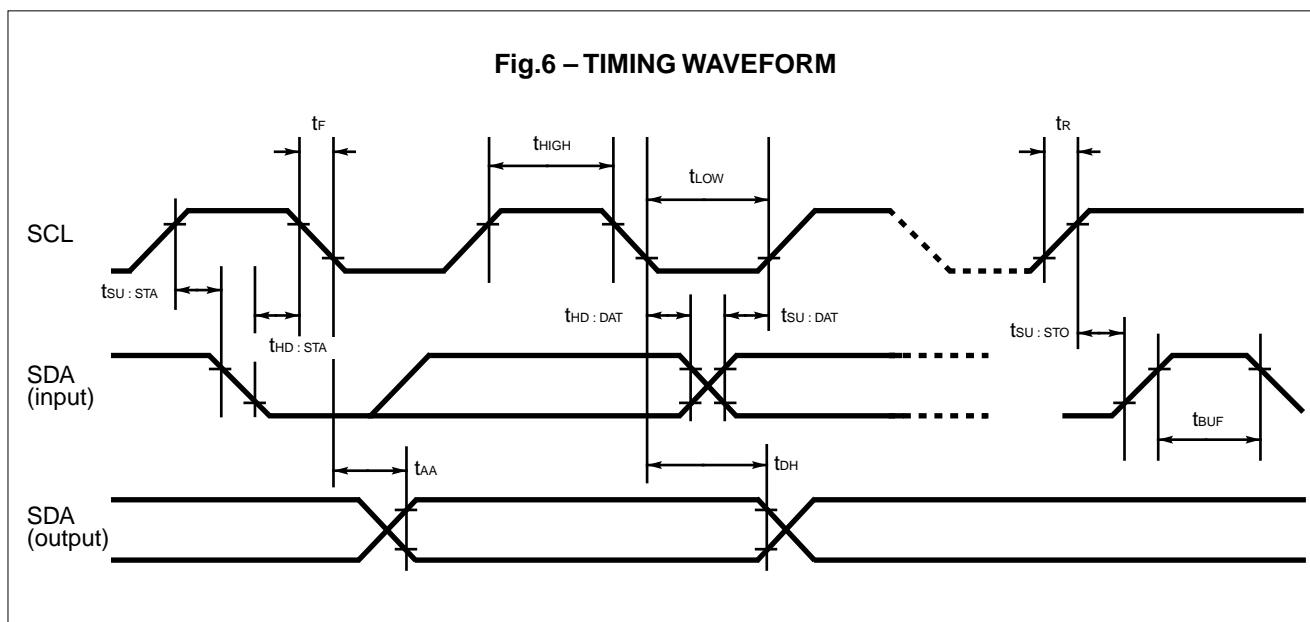
Parameter	Note	Symbol	Condition	Value		Unit
				Min.	Max.	
Input Leakage Current		S_{ILI}	$0 V \leq V_{IN} \leq V_{CC}$	-10	10	μA
Output Leakage Current		S_{ILO}	$0 V \leq V_{OUT} \leq V_{CC}$	-10	10	μA
Output Low Voltage	*1	S_{VOL}	$I_{OL} = 3.0 \text{ mA}$	—	0.4	V

Note: *1. Referenced to V_{SS} .

MB8504S064AC-100/-84/-67

5. AC CHARACTERISTICS

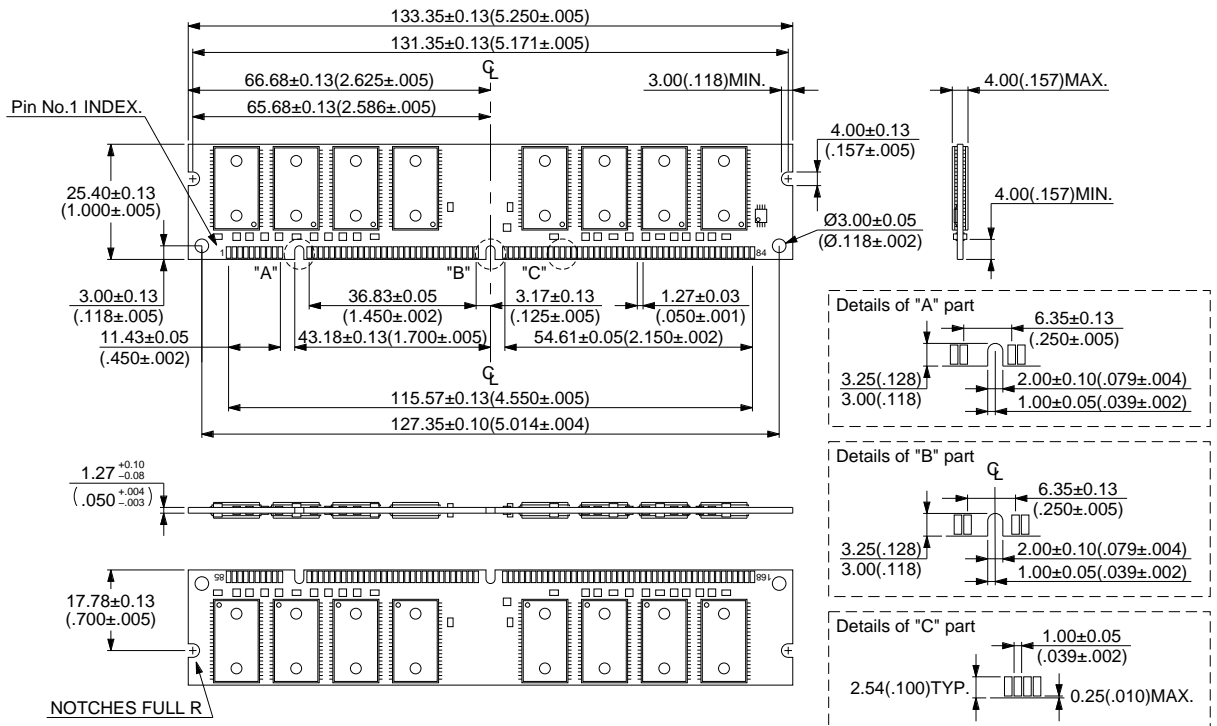
No.	Parameter	Symbol	Min.	Max.	Unit
1	SCL Clock Frequency	f_{SCL}	0	100	KHz
2	Noise Suppression Time Constant at SCL, SDA Inputs	T_i	—	100	ns
3	SCL Low to SDA Data Out Valid	t_{AA}	—	3.5	μs
4	Time the Bus Must Be Free Before a New Transmission Can Start	t_{BUF}	4.7	—	μs
5	Start Condition Hold Time	$t_{HD:STA}$	4.0	—	μs
6	Clock Low Period	t_{LOW}	4.7	—	μs
7	Clock High Period	t_{HIGH}	4.0	—	μs
8	Start Condition Set Up Time	$t_{SU:STA}$	4.7	—	μs
9	Data In Hold Time	$t_{HD:DAT}$	0	—	μs
10	Data In Set Up Time	$t_{SU:DAT}$	250	—	ns
11	SDA and SCL Rise Time	t_R	—	1	μs
12	SDA and SCL Fall Time	t_F	—	300	ns
13	Stop Condition Set Up Time	$t_{SU:STO}$	4.7	—	μs
14	Data Out Hold Time	t_{DH}	100	—	ns
15	Write Cycle Time	t_{WR}	—	15	ms



MB8504S064AC-100/-84/-67

■ PACKAGE DIMENSIONS

168-PIN DUAL IN-LINE MEMORY MODULE (CASE No.: MDS-168P-P09)



© 1996 FUJITSU LIMITED M168009SC-1-1

Dimension in mm (inches).

FUJITSU LIMITED

For further information please contact:

Japan

FUJITSU LIMITED
Corporate Global Business Support Division
Electronic Devices
KAWASAKI PLANT, 4-1-1, Kamikodanaka
Nakahara-ku, Kawasaki-shi
Kanagawa 211-88, Japan
Tel: (044) 754-3763
Fax: (044) 754-3329

North and South America

FUJITSU MICROELECTRONICS, INC.
Semiconductor Division
3545 North First Street
San Jose, CA 95134-1804, U.S.A.
Tel: (408) 922-9000
Fax: (408) 432-9044/9045

Europe

FUJITSU MIKROELEKTRONIK GmbH
Am Siebenstein 6-10
63303 Dreieich-Buchsschlag
Germany
Tel: (06103) 690-0
Fax: (06103) 690-122

Asia Pacific

FUJITSU MICROELECTRONICS ASIA PTE. LIMITED
#05-08, 151 Lorong Chuan
New Tech Park
Singapore 556741
Tel: (65) 281-0770
Fax: (65) 281-0220

All Rights Reserved.

The contents of this document are subject to change without notice. Customers are advised to consult with FUJITSU sales representatives before ordering.

The information and circuit diagrams in this document presented as examples of semiconductor device applications, and are not intended to be incorporated in devices for actual use. Also, FUJITSU is unable to assume responsibility for infringement of any patent rights or other rights of third parties arising from the use of this information or circuit diagrams.

FUJITSU semiconductor devices are intended for use in standard applications (computers, office automation and other office equipment, industrial, communications, and measurement equipment, personal or household devices, etc.).

CAUTION:

Customers considering the use of our products in special applications where failure or abnormal operation may directly affect human lives or cause physical injury or property damage, or where extremely high levels of reliability are demanded (such as aerospace systems, atomic energy controls, sea floor repeaters, vehicle operating controls, medical devices for life support, etc.) are requested to consult with FUJITSU sales representatives before such use. The company will not be responsible for damages arising from such use without prior approval.

Any semiconductor devices have inherently a certain rate of failure. You must protect against injury, damage or loss from such failures by incorporating safety design measures into your facility and equipment such as redundancy, fire protection, and prevention of over-current levels and other abnormal operating conditions.

If any products described in this document represent goods or technologies subject to certain restrictions on export under the Foreign Exchange and Foreign Trade Control Law of Japan, the prior authorization by Japanese government should be required for export of those products from Japan.